/ Descriptions

Silicon PNP transistor in a SOT-23 Plastic Package.

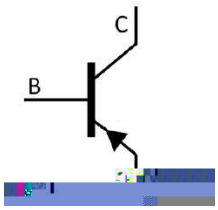
/ Features

Complementary pair with S8050MG,HF Product.

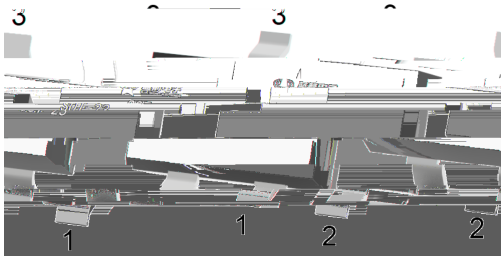
/ Applications

Power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

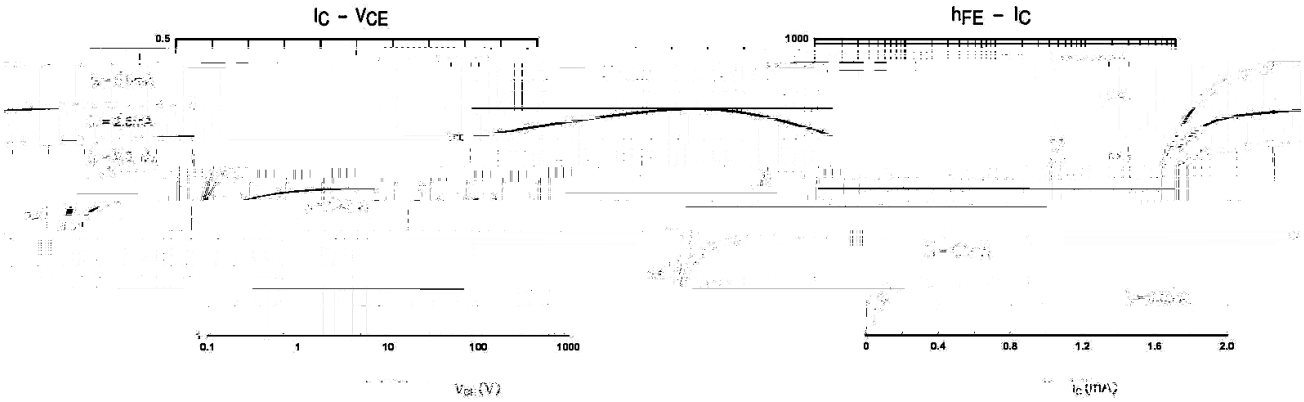
/ h_{FE} Classifications & Marking

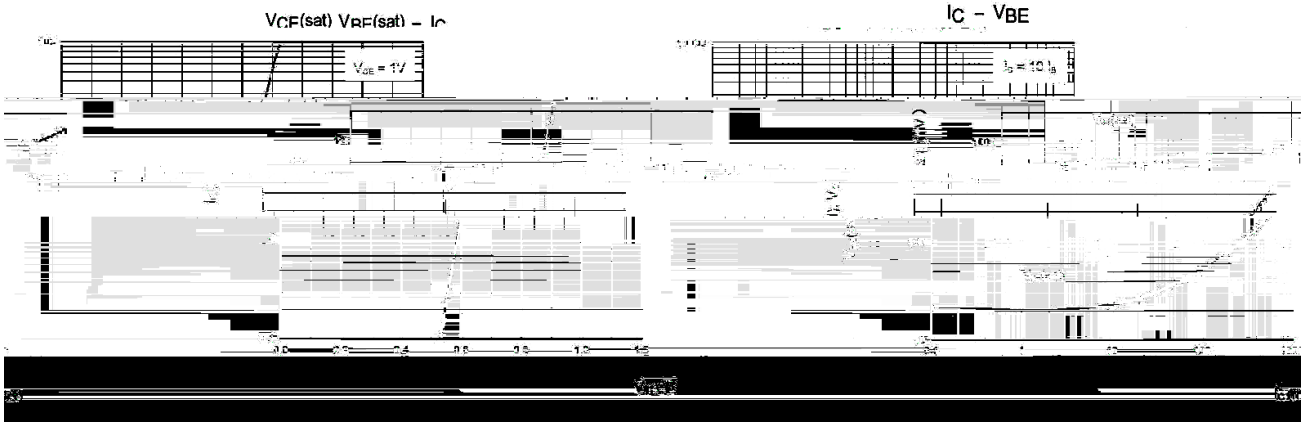
h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	85 160	120 200	160 300
Marking	GY4B	GY4C	GY4D

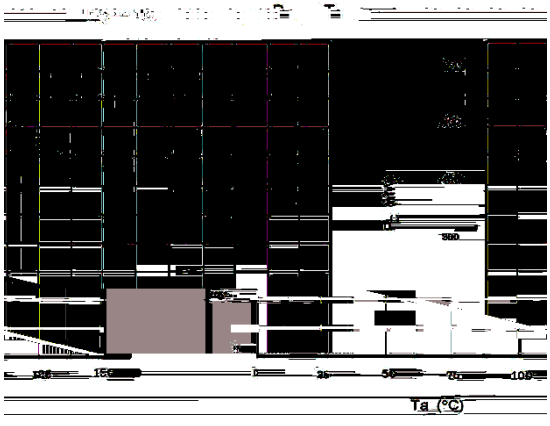
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-800	mA
Base Current	I_B	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

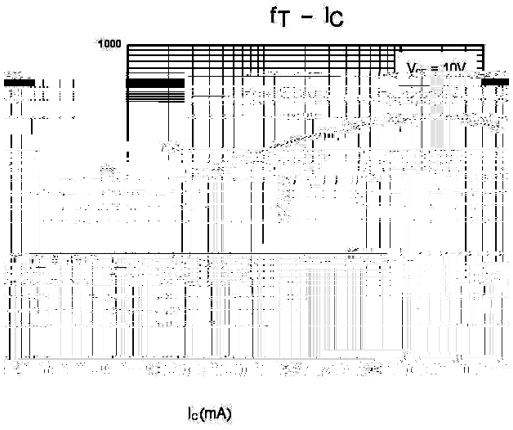
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-2.0mA I_B=0	-25			V

/ Electrical Characteristic Curve

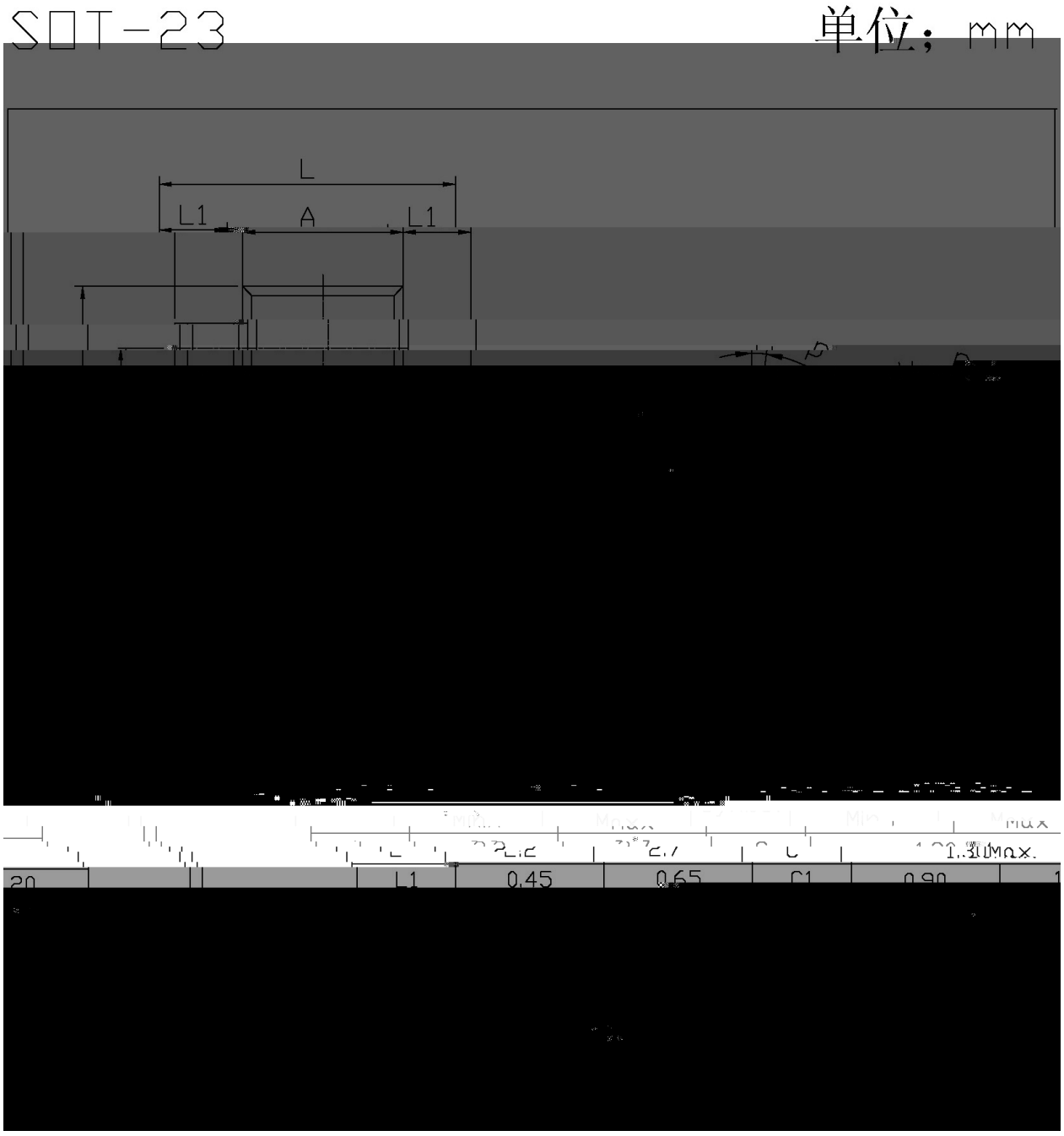




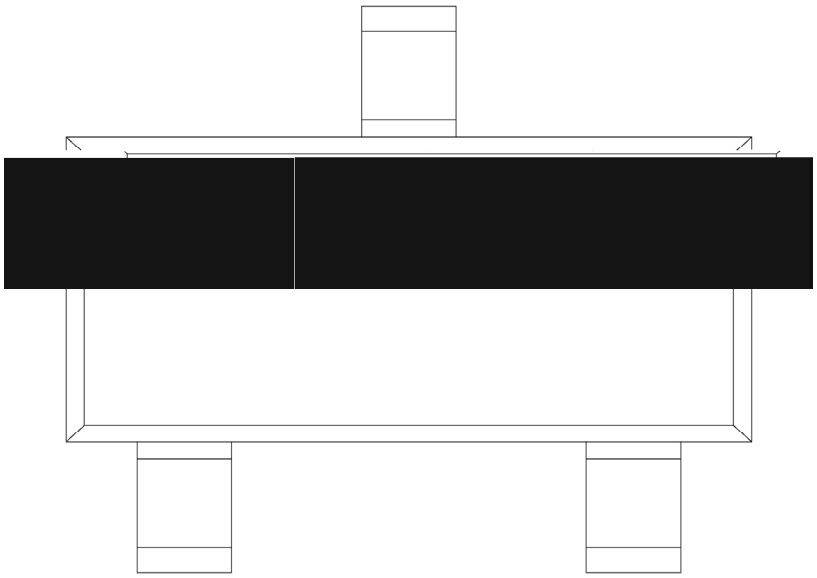




/ Package Dimensions



/ Marking Instructions



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Note:

1 150 180 60